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SUBSTITUTE SPECIFICATION

MULTILAYER WIRING BOARD AND SEMICONDUCTOR DEVICE

BACKGROUND OF THE INVENTION

[0001] The present invention relates to a semiconductor device such as a multifinger type device used, for example, in high-frequency power amplifiers for portable communication terminals.

[0002] Power enabling communication from a position distant from a communication relay point is required of portable communication terminals such as portable telephones. In order to achieve successful operation of such portable communication terminals, high-frequency power amplifiers used in portable communication terminals have been developed to have increased capacity.

[0003] As a measure for increasing the capacity of such high-frequency power amplifiers, it is possible to provide an increase in current for high output by modularizing and arranging many bipolar transistors (hereinafter, referred to simply as transistors) in parallel at predetermined spacing.

[0004] However, if transistors are arranged in parallel at predetermined spacing, centrally positioned transistors are thermally affected by adjacent transistors to become highest in thermal resistance (hereinafter referred to as calorific value).

[0005] In this manner, when transistors having high calorific values are present among the transistors arranged in parallel, current flows through the transistors of high calorific values in a concentrated manner, and hence the